

TSM2302

20V N-Channel MOSFET



SOT-23

Pin Definition:



1. Gate 2. Source 3. Drain

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)	
20	65 @ V _{GS} = 4.5V	2.8	
	95 @ V _{GS} = 2.5V	2.0	

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

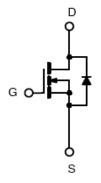
Application

- Load Switch
- PA Switch

Ordering Information

Part No.	Package	Packing
TSM2302CX RF	SOT-23	3Kpcs / 7" Reel

Block Diagram



N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit		
Drain-Source Voltage		V_{DS}	20	V	
Gate-Source Voltage		V_{GS}	±8	V	
Continuous Drain Current, V _{GS} @4.5V.	4.5V. I _D 2.8		2.8	А	
Pulsed Drain Current, V _{GS} @4.5V		I _{DM}	8	А	
Continuous Source Current (Diode Conde	uction) ^{a,b}	I _S	1.0	Α	
Maximum Davier Disaination	Ta = 25°C		0.9	w	
Maximum Power Dissipation	Ta = 75°C	$\overline{}$ P_D	0.57		
Operating Junction Temperature		T _J	+150	°C	
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance	R⊖ _{JF}	75	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	RO _{JA}	250	°C/W

Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, t ≤ 5 sec.



TSM2302

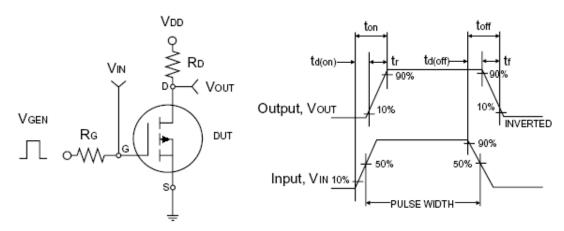
20V N-Channel MOSFET



Electrical Specifications

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	20		-	V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	0.65	0.95	1.2	V
Gate Body Leakage	$V_{GS} = \pm 8V, V_{DS} = 0V$	I _{GSS}	-		±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 16V, V_{GS} = 0V$	I _{DSS}			1.0	μΑ
On-State Drain Current	$V_{DS} \square 5V$, $V_{GS} = 4.5V$	I _{D(ON)}	6		-	Α
Drain Source On State Besistance	$V_{GS} = 4.5V$, $I_D = 2.8A$		-	40	65	mΩ
Drain-Source On-State Resistance	$V_{GS} = 2.5V, I_D = 2.0A$	$R_{DS(ON)}$		50	95	
Forward Transconductance	$V_{DS} = 5V, I_D = 2.8A$	g _{fs}	1	6.5	I	S
Diode Forward Voltage	$I_S = 1.6A, V_{GS} = 0V$	V_{SD}	-	0.76	1.2	V
Dynamic ^b	_					
Total Gate Charge	1/ -6\/ -201	Q_g		3.69		
Gate-Source Charge	$V_{S} = 1.6A, V_{GS} = 0V$ $V_{DS} = 6V, I_{D} = 2.8A, V_{GS} = 4.5V$	Q_gs		0.7		nC
Gate-Drain Charge	V _{GS} = 4.5 V	Q_{gd}		1.06		
Input Capacitance	\/ - C\/ \/ - O\/	C _{iss}	I	427.12	I	
Output Capacitance	$V_{DS} = 6V, V_{GS} = 0V,$ f = 1.0MHz	C_{oss}	I	80.56	I	pF
Reverse Transfer Capacitance	1 - 1.0IVINZ	C _{rss}	I	57	I	
Switching ^c						
Turn-On Delay Time	V - 6V D - 400	t _{d(on)}	I	6.16	I	
Turn-On Rise Time	$V_{DD} = 6V, R_L = 10\Omega,$ $I_D = 1A, V_{GEN} = 4.5V,$	t _r	-	7.56	1	nC
Turn-Off Delay Time	5 , 52	t _{d(off)}		16.61		nS
Turn-Off Fall Time	$R_G = 6\Omega$	t _f		4.07		

- a. pulse test: PW $\square 300 \mu S,$ duty cycle $\square 2\%$ b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms

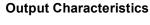


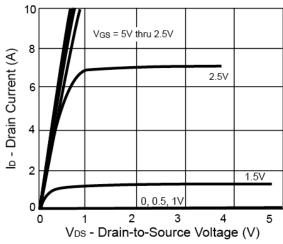




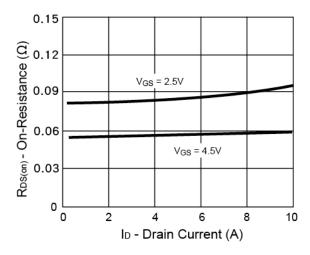


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

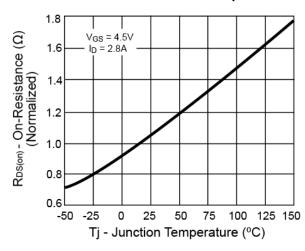




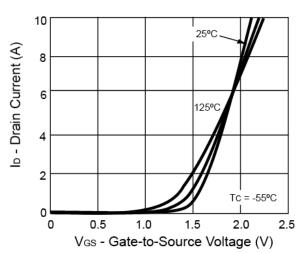
On-Resistance vs. Drain Current



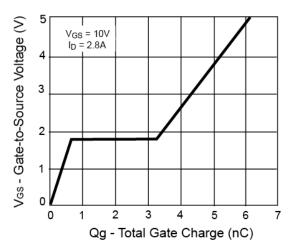
On-Resistance vs. Junction Temperature



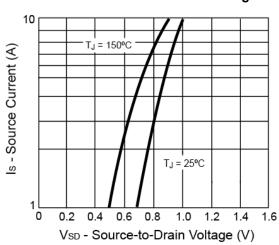
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage





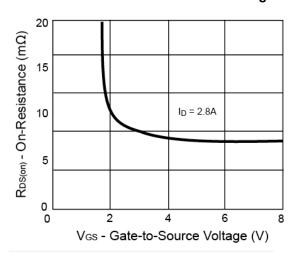


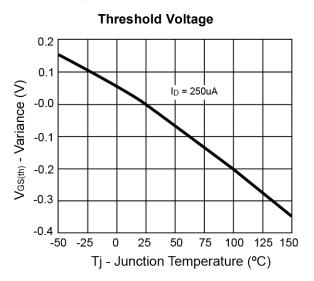




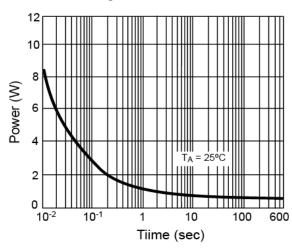
Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

On-Resistance vs. Gate-Source Voltage

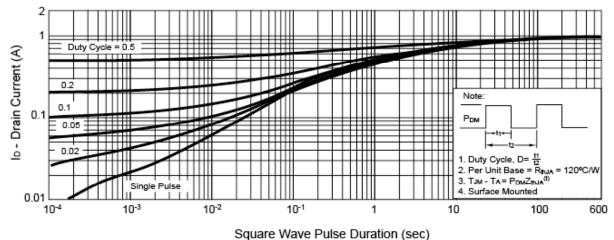




Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



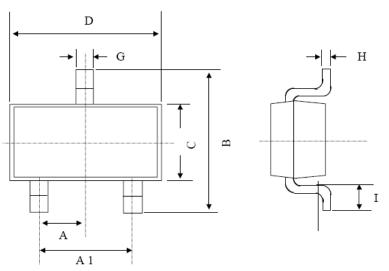
Square wave Fulse Duration (sec



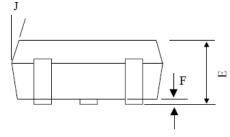




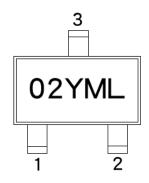
SOT-23 Mechanical Drawing



	SOT-23 DIMENSION				
DIM	MILLIMETERS		INCHES		
DIIVI	MIN	MAX	MIN	MAX.	
Α	0.95	BSC	0.037 BSC		
A1	1.9 I	BSC	0.074 BSC		
В	2.60	3.00	0.102	0.118	
С	1.40	1.70	0.055	0.067	
D	2.80	3.10	0.110	0.122	
E	1.00	1.30	0.039	0.051	
F	0.00	0.10	0.000	0.004	
G	0.35	0.50	0.014	0.020	
Н	0.10	0.20	0.004	0.008	
Ī	0.30	0.60	0.012	0.024	
J	5°	10°	5°	10°	



Marking Diagram



02 = Device Code

Y = Year Code

M = Month Code

(**A**=Jan, **B**=Feb, **C**=Mar, **D**=Apl, **E**=May, **F**=Jun, **G**=Jul, **H**=Aug, **I**=Sep, **J**=Oct, **K**=Nov, **L**=Dec)

L = Lot Code



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